

FAST SWITCHING DIODES

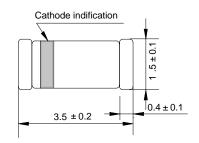
FEATURES

LL34 Glass Case SOD-80C For general purpose applications. The LL103A, B, C is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.

The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other applications are click suppression, efficient diodes in rechargeable low voltage battery systems.

This diode is also available in DO-35 case with the type designation SD103A, B, C, and in the SOD-123 case with type designation SD103AW, SD103BW, SD103CW.

LL103A-LL103C



LL-34(SOD-80) Dimensions in millimeters

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

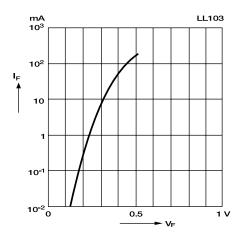
	Symbol	Value	Unit
LL103A LL103B LL103C	V _{RRM} V _{RRM} V _{RRM}	40 30 20	V V V
	P _{tot}	4001)	mW
Junction Temperature		125	°C
	T _S	-55 to +150	°C
	I _{FSM}	15	А
	LL103B	LL103B VRRM VRRM VRRM Ptot T _j T _S	LL103B VRRM 30 20 Ptot 4001) Tj 125 Ts -55 to +150

	Symbol	Min.	Тур.	Max.	Unit
	I _R I _R I _R	_ _ _	_ _ _	5 5 5	μΑ μΑ μΑ
Forward Voltage Drop at $I_F = 20$ mA at $I_F = 200$ mA	V _F V _F			0.37 0.6	V
Junction Capacitance at V _R = 0 V, f = 1 MHz	C _{tot}	_	50	-	pF
Reverse Recovery Time at $I_F = I_R = 50$ mA to 200 mA, recover to 0.1 I_R	t _{rr}	_	10	_	ns

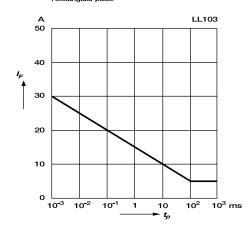


LL103A-LL103C Typical Characteristics

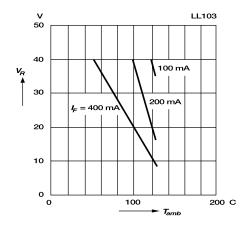
Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier



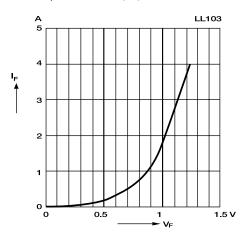
Typical non repetitive forward surge current versus pulse width
Rectangular pulse



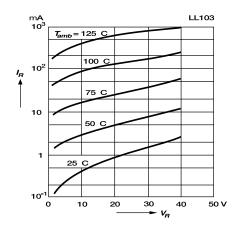
Blocking voltage deration versus temperature at various average forward currents



Typical high current forward conduction curve $t_{\rm p}$ =300 ms, duty cycle =2%



Typical variation of reverse current at various temperatures



Typical capacitance versus reverse voltage

